MITSUBISHI ELECTRIC

< HVIC >

M81748FP

1200V HIGH VOLTAGE HALF BRIDGE DRIVER

DESCRIPTION

M81748FP is 1200V high voltage Power MOSFET and IGBT module driver for half bridge applications.

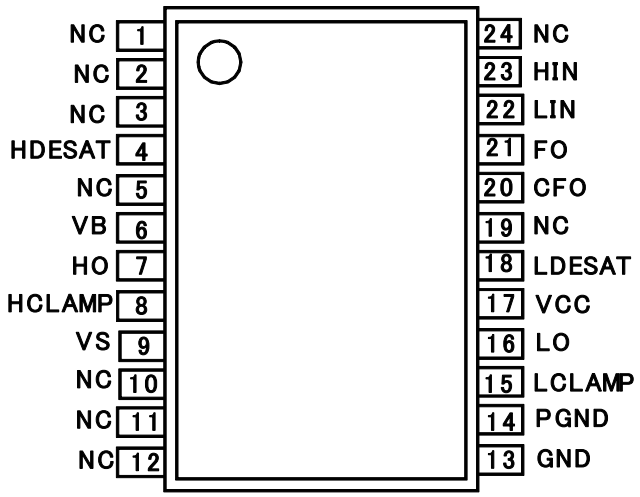
FEATURES

- Floating supply voltage up to 1200V
- Low quiescent power supply current
- Sink and source current output up to ±2A (typ)
- Active Miller effect clamp up to 2A (typ)
- Input noise filters (HIN,LIN,FO)
- Desat detection and protection with output soft shutdown
- Under voltage lockout
- Synchronization signal to synchronize shutdown with other phases

APPLICATIONS

Power MOSFET and IGBT gate driver for Inverter or general purpose.

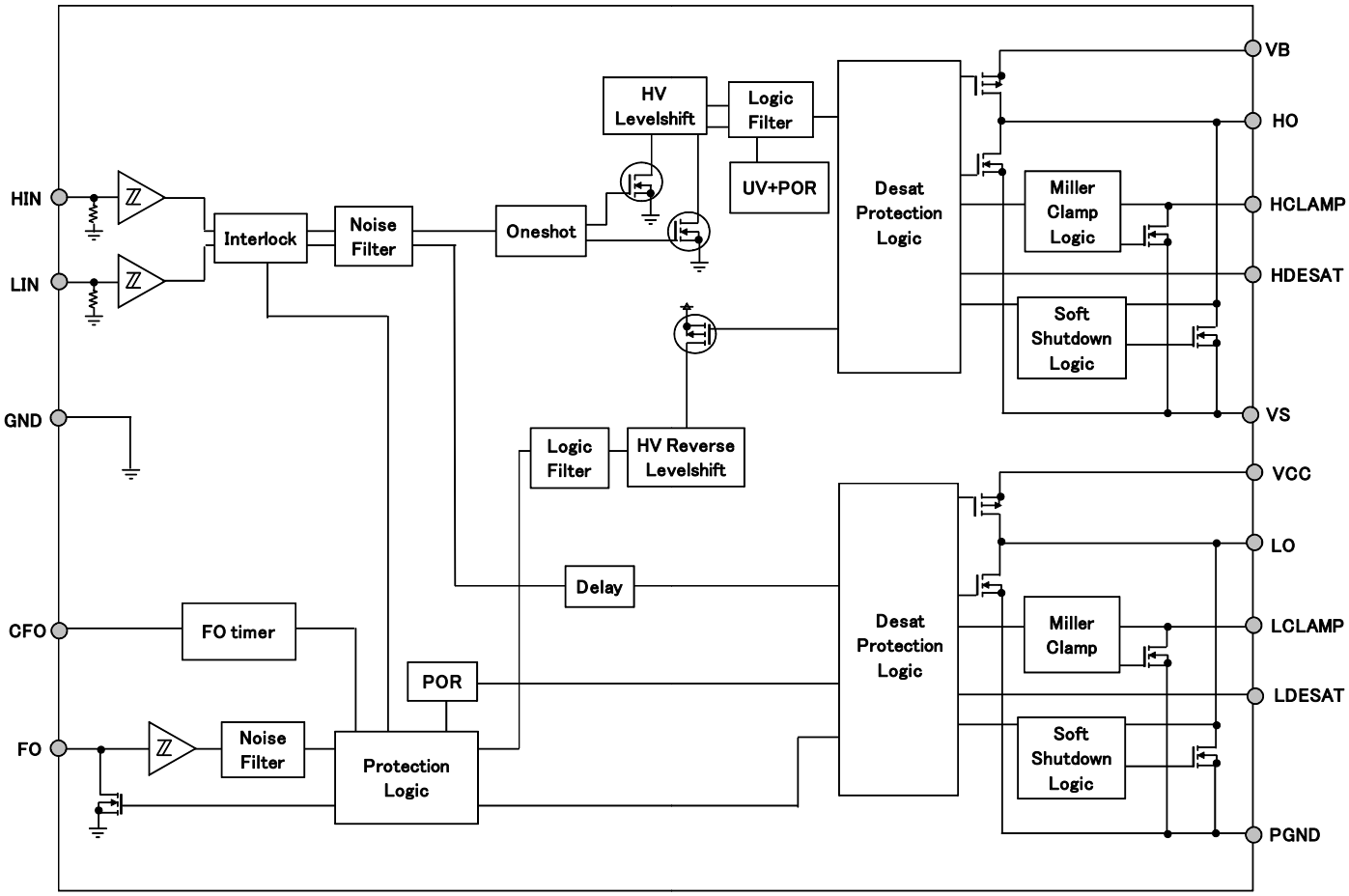
PIN CONFIGURATION (TOP VIEW)



Outline:24P2Q

SSOP-Lead PACKAGE

BLOCK DIAGRAM



ABSOLUTE MAXIMUM RATINGS

Absolute maximum ratings indicate limitation beyond which destruction of device may occur. All voltage parameters are absolute voltage reference to GND and PGND unless otherwise specified.

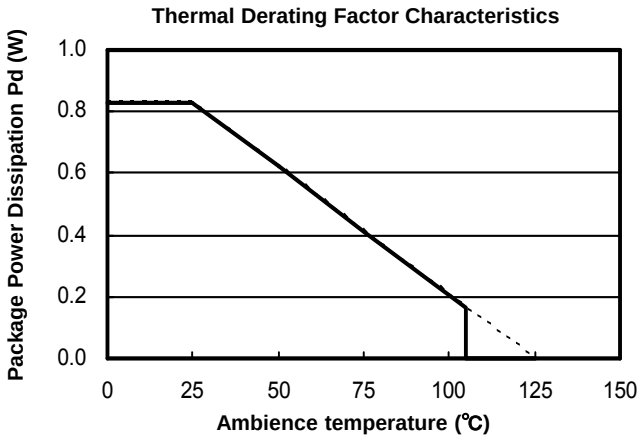
Symbol	Parameter	Test conditions	Raitings	Unit
V_B	High side floating supply absolute voltage		−0.5～1224	V
V_S	High side floating supply offset voltage		V_B −24～V_B +0.5	V
V_{BS}	High side floating supply voltage	$V_{BS}=V_B-V_S$	−0.5～24	V
V_{HO}	High side output voltage		V_S −0.5～V_B +0.5	V
V_{HCLAMP}	High side CLAMP input/output voltage		V_S −0.5～V_B +0.5	V
V_{HDESAT}	High side DESAT input/otuput voltage		V_S −0.5～V_B +0.5	V
V_{CC}	Low side fixed supply voltage		−0.5～24	V
V_{LO}	Low side output voltage		−0.5～V_{CC} +0.5	V
V_{LCLAMP}	Low side CLAMP input/output voltage		−0.5～V_{CC} +0.5	V
V_{LDESAT}	Low side DESAT input/output voltage		−0.5～V_{CC} +0.5	V
V_{IN}	Logic input voltage	HIN, LIN	−0.5～V_{CC} +0.5	V
V_{FO}	FO input/output voltage		−0.5～V_{CC} +0.5	V
dV_S/dt	Allowable offset voltage slew rate	V_S −GND and PGND	±50	V/ns
Pd	Package power dissipation	Ta= 25°C ,On our standard PCB	～1.11	W
Kθ	Linear derating factor	Ta≧25°C ,On our standard PCB	～11.1	mW/°C
Rth(j-a)	Junction-ambient air thermal resistance	On our standard PCB	～90	°C/W
Tj	Junction temperature		−40～125	℃
Topr	Operation temperature		−40～105	℃
Tstg	Storage temperature		−55～150	℃
TL	Solder reflow condition	Pb-free	255:10s, max260	℃

RECOMMENDED OPERATING CONDITIONS

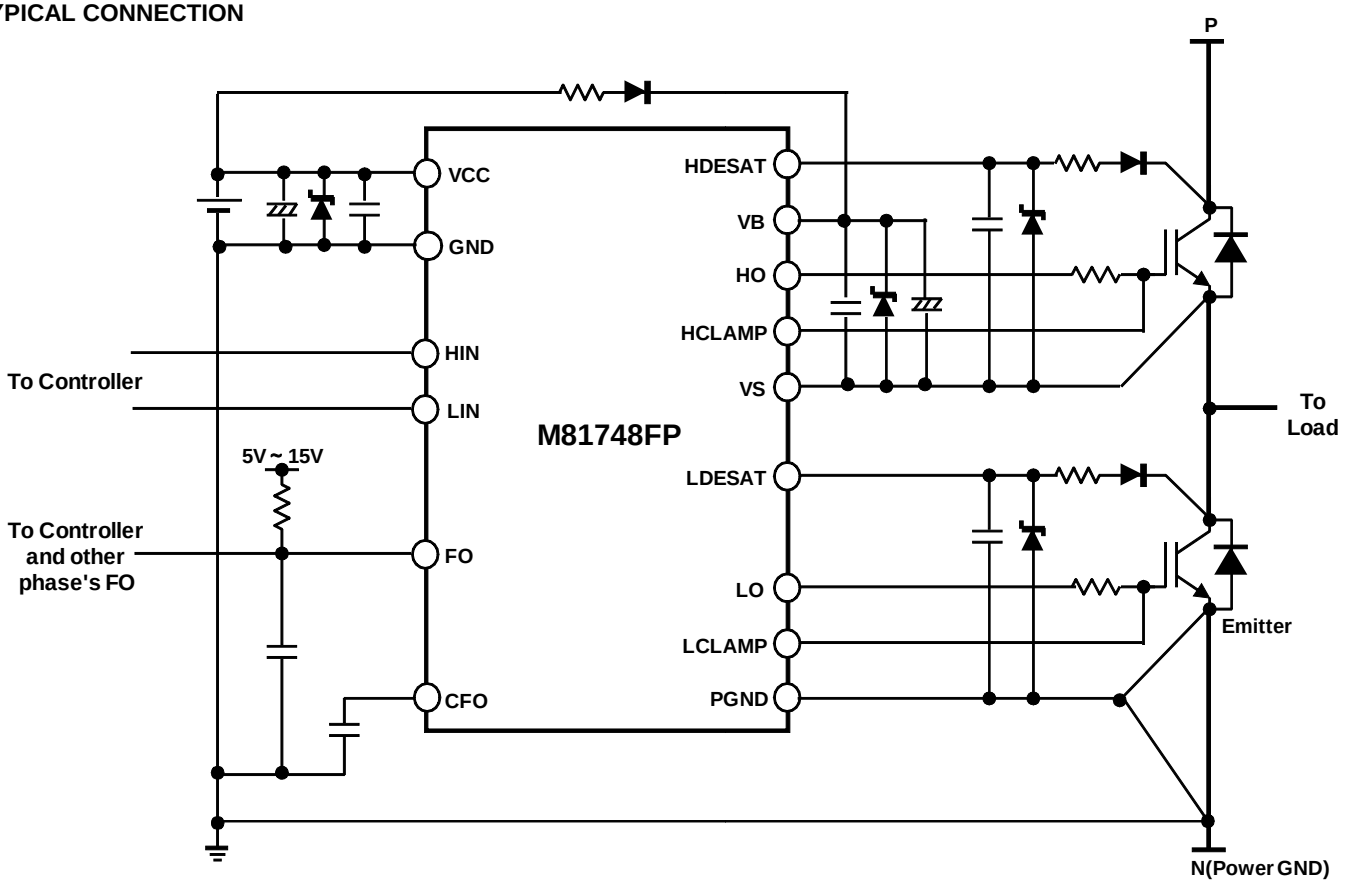
For proper operation the device should be used within the recommended conditions. All voltage parameters are absolute voltages referenced to GND and PGND unless otherwise specified.

Symbol	Parameter	Test conditions	Limits			Unit
			Min.	Typ.	Max.	
V_B	High side floating supply absolute voltage		V_S+13.5	V_S+15	V_S+16.5	V
V_S	High side floating supply offset voltage	V_{BS}> 13.5V	−5	−	900	V
V_{BS}	High side floating supply voltage	$V_{BS}=V_B-V_S$	13.5	15	16.5	V
V_{HO}	High side output voltage		V_S	−	V_S+16.5	V
V_{HCLAMP}	High side CLAMP input/output voltage		V_S	−	V_S+16.5	V
V_{HDESAT}	High side DESAT input/output voltage		V_S	−	V_S+16.5	V
V_{CC}	Low side fixed supply voltage		13.5	15	16.5	V
V_{LO}	Low side output voltage		0	−	V_{CC}	V
V_{LCLAMP}	Low side CLAMP input/output voltage		0	−	V_{CC}	V
V_{LDESAT}	Low side DESAT input/otuput voltage		0	−	V_{CC}	V
V_{IN}	Logic input voltage	HIN, LIN,	0	−	V_{CC}	V
V_{FO}	FO input/output voltage		0	−	V_{CC}	V

PERFORMANCE CURVES



TYPICAL CONNECTION



Note: If HVIC is working in high noise environment, it is recommended to connect a 1nF ceramic capacitor to FO pin.
It is recommended to connect PGND pin to Emitter and Power GND(N). If PGND pin is not connected to Power GND(N), please pay attention to a noise between PGND pin and Power GND(N).

ELECTRICAL CHARACTERISTICS (Ta=25°C, V_{CC}=V_{BS}(=V_B-V_S)=15V, unless otherwise specified)

Symbol	Parameter	Test conditions	Limits			Unit
			Min.	Typ.	Max.	
I_{FS}	High side leakage current	V_B = V_S = 1200V	−	−	10	uA
I_{BS}	V_{BS} quiescent supply current	HIN = LIN = 0V	−	0.7	1.4	mA
I_{CC}	V_{CC} quiescent supply current	HIN = LIN = 0V	−	1.2	2.4	mA
V_{OH}	High level output voltage	I_O = 20mA, HO, LO	14.5	−	−	V
V_{OL}	Low level output voltage	I_O = −20mA, HO, LO	−	−	0.5	V
V_{IH}	High level input threshold voltage	HIN, LIN	4.0	−	−	V
V_{IL}	Low level input threshold voltage	HIN, LIN	−	−	1.0	V
I_{IH}	High level input bias current	V_{IN} = 5V	0.6	1.0	1.4	mA
I_{IL}	Low level input bias current	V_{IN} = 0V	0.00	0.00	0.01	mA
tFilter	Input signals filter time	HIN on−pulse	100	−	500	ns
		HIN off−pulse	100	−	500	ns
		LIN on−pulse	100	−	500	ns
		LIN off−pulse	100	−	500	ns
		FO off−pulse	100	−	500	ns
V_{HCT}	High side active Miller clamp NMOS input threshold voltage	V_{IN} = 0V	−	3.0	4.0	V
V_{LCT}	Low side active Miller clamp NMOS input threshold voltage	V_{IN} = 0V	−	3.0	4.0	V
V_{OLFO}	Low level FO output voltage	I_{FO} = 1mA	−	−	0.4	V
V_{IHFO}	High level FO input threshold voltage		4.0	−	−	V
V_{ILFO}	Low level FO input threshold voltage		−	−	1.0	V
V_{BSuvr}	V_{BS} supply UV reset voltage		10.5	11.5	12.5	V
V_{BSuvt}	V_{BS} supply UV trip voltage		9.7	10.7	11.7	V
V_{BSuvh}	V_{BS} supply UV hysteresis voltage	V_{BSuvh} = V_{BSuvr}−V_{BSuvt}	0.4	0.8	−	V
tV_{BSuv}	V_{BS} supply UV filter time		4	8	16	us
V_{LPOR}	Low side VCC POR trip voltage		7.0	9.0	11.0	V
I_{OH}	Output high level short circuit pulsed current	HO(LO) = 0V, V_{IN} = 5V, PW ≦ 10μs	1.6	2.0	−	A
I_{OL1}	Output low level short circuit pulsed current	HO(LO) = 15V, V_{IN} = 0V, PW ≦ 10μs	−1.6	−2.0	−	A
I_{OL2}	Active Miller clamp NMOS output low level short circuit pulsed current	HCLAMP(LCLAMP) = 15V, V_{IN} = 0V, PW ≦ 10μs	−1.6	−2.0	−	A
tdLH(HO)	High side turn-on propagation delay	HO short to HCLAMP, CL = 1nF	0.7	1.0	1.3	us
tdHL(HO)	High side turn-off propagation delay	HO short to HCLAMP, CL = 1nF	0.7	1.0	1.3	us
tdLH(LO)	Low side turn-on propagation delay	LO short to LCLAMP, CL = 1nF	0.7	1.0	1.3	us
tdHL(LO)	Low side turn-off propagation delay	LO short to LCLAMP, CL = 1nF	0.7	1.0	1.3	us
tr	Output turn-on rise time	CL = 1nF	5	20	40	ns
tf	Output turn-off fall time	CL = 1nF	5	20	40	ns
ΔtdLH	Delay matching, high side turn-on and low side turn-off	tdLH(HO)−tdHL(LO)	−0.15	0.00	0.15	us
ΔtdHL	Delay matching, high side turn-off and low side turn-on	tdLH(LO)−tdHL(HO)	−0.15	0.00	0.15	us

Note: Typ. is not specified.

ELECTRICAL CHARACTERISTICS (Ta=25°C, V_{CC}=V_{BS}(=V_B-V_S)=15V, unless otherwise specified)

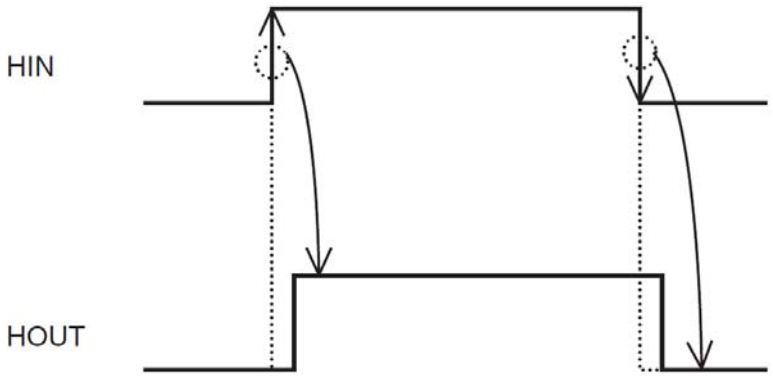
Symbol	Parameter	Test conditions	Limits			Unit
			Min.	Typ.	Max.	
I_{CHG}	Blanking Capacitor Charging Current	V_{DESAT} = 2V	−0.13	−0.24	−0.33	mA
I_{DSCHG}	Blanking Capacitor Discharge Current	V_{DESAT} = 7V	10	30	−	mA
V_{DESAT}	DESAT Threshold		6	6.5	7.5	V
$t_{DESAT(90\%)}$	DESAT Sense to 90%VO Delay	CL = 1nF	−	0.17	0.34	us
$t_{DESAT(10\%)}$	DESAT Sense to 10%VO Delay	CL= 1nF	−	0.30	0.60	us
$t_{DESAT(FAULT)\_H}$	HDESAT Sense to Low Level FAULT Signal Delay	R_F = 15kΩ	−	0.40	0.50	us
$t_{DESAT(FAULT)\_L}$	LDESAT Sense to Low Level FAULT Signal Delay	R_F = 15kΩ	−	0.25	0.50	us
$t_{DESAT(LOW)}$	DESAT Sense to DESAT Low Propagation Delay	C_{DESAT} = 1nF	−	0.25	−	us
t_{FO}	FO timer	CFO=1nF	−	110	−	us

Note: Typ. is not specified.

FUNCTION TABLE (Q: Keep previous status)

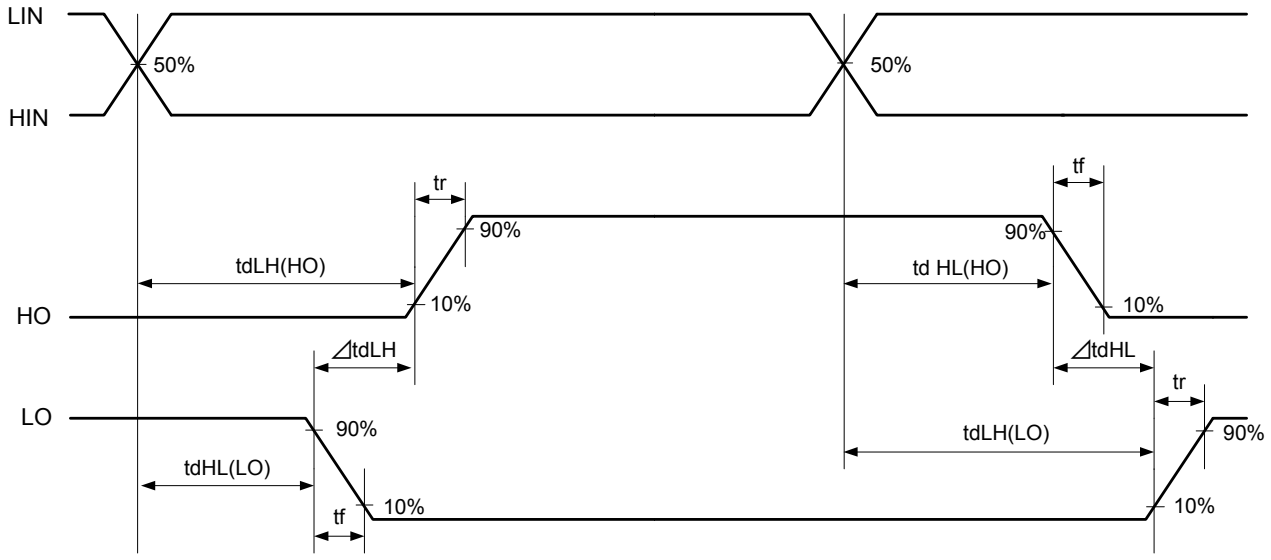
HIN	LIN	FO (Input)	HDESAT	LDESAT	V_{BS}/ UV	HO	LO	FO (Output)	Behavioral status
L	L	−	L	L	H	L	L	H	
L	H	−	L	L	H	L	H	H	
H	L	−	L	L	H	H	L	H	
H	H	−	L	L	H	L	L	H	Interlock active
H	X	−	H	X	H	L	L	L	Hige side DESAT
X	H	−	X	H	H	L	L	L	Low side DESAT
X	X	L	X	X	X	L	L	−	Output shuts down when FO = L
X	H	−	L	L	L	L	H	H	V_{BS} power reset is tripping when LIN = H

Note1 :"L" status of V_{BS}/UV indicates a high side UV reset condition.
Note2 : In the case of both input signals (HIN and LIN) are "H", output signals (HO and LO) become "L".
Note3 : X (HIN) : L→H or H → L. Other : H or L.
Note4 : Output signal (HO) is triggered by the edge of input signal.
Note5 : Please see FUNCTIONAL DESCRIPTION 7(p.9) for detailed sequences of desaturation.



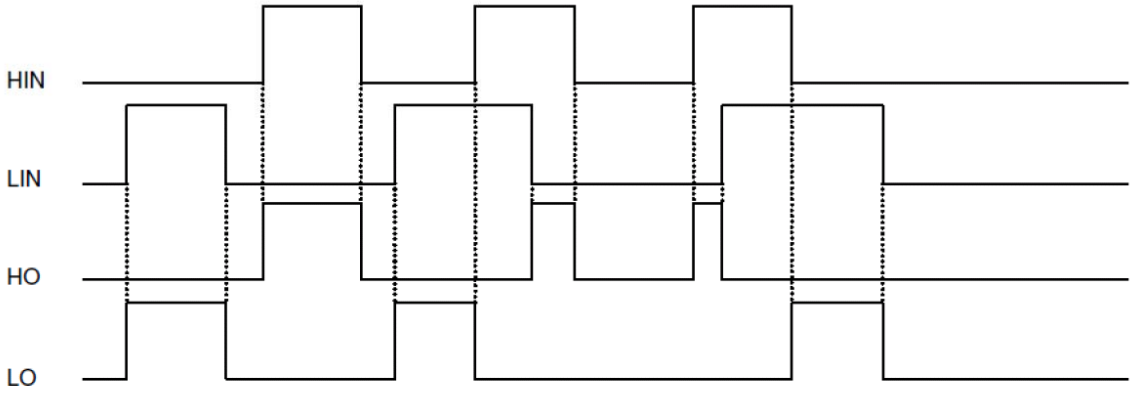
FUNCTIONAL DESCRIPTION

1. INPUT/OUTPUT TIMING DIAGRAM



2. INPUT INTERLOCK TIMING DIAGRAM

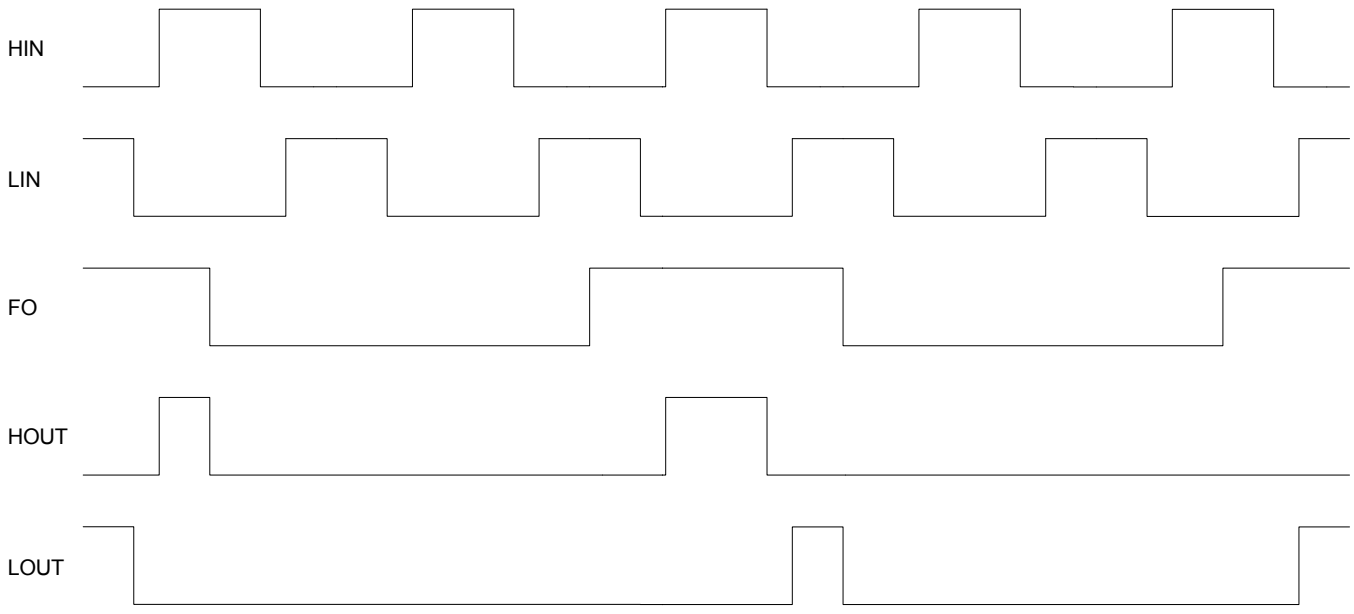
When the input signals (HIN/LIN) are high level at the same time, the outputs (HO/LO) shuts down.



Note1 :The minimum input pulse width at HIN/LIN should be to more than 500ns (because of HIN/LIN input noise filter circuit).
Note2 :Delay times between input and output signals are not shown in the figure above.

3. FO INPUT TIMING DIAGRAM

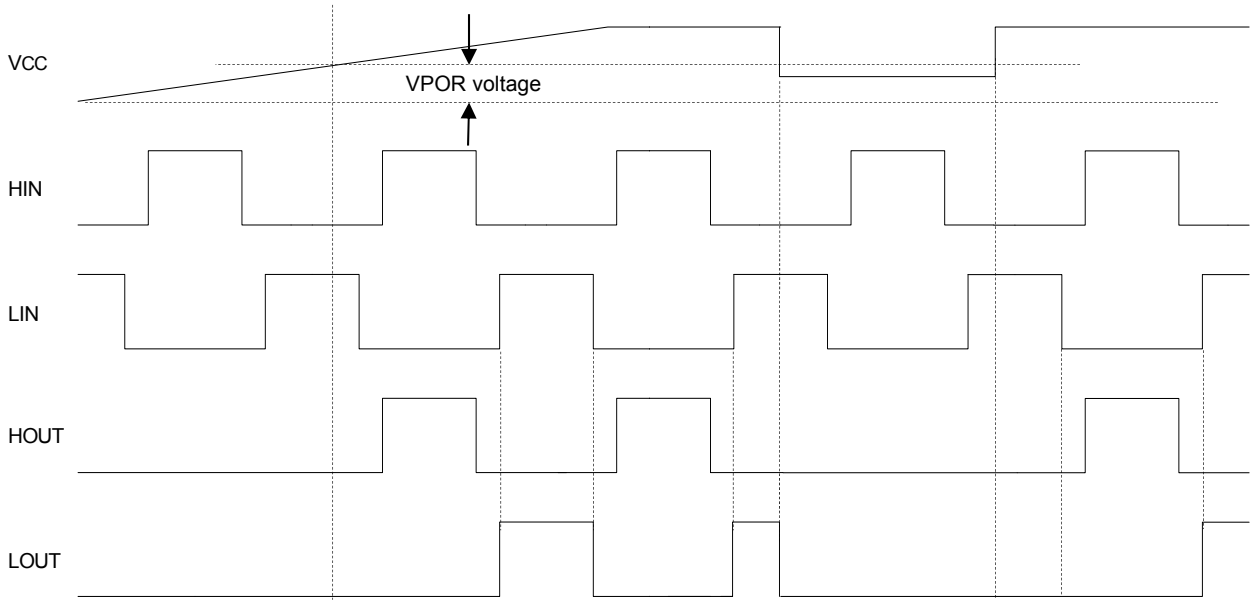
When FO is pulled down to low level in case the FO of other phases becomes low level (fault happened) or the MCU/DSP sets FO to low level, the outputs (HOUT, LOUT) of the driver will be shut down. As soon as FO goes high again, the output will respond to the following active input signal.



Note1 :Delay times between input and output signals are not shown in the figure above.
Note2 :The minimum FO pulse width should be more than ns (because of FO input filter circuit).

4. LOW SIDE V_{CC} SUPPLY POWER RESET SEQUENCE

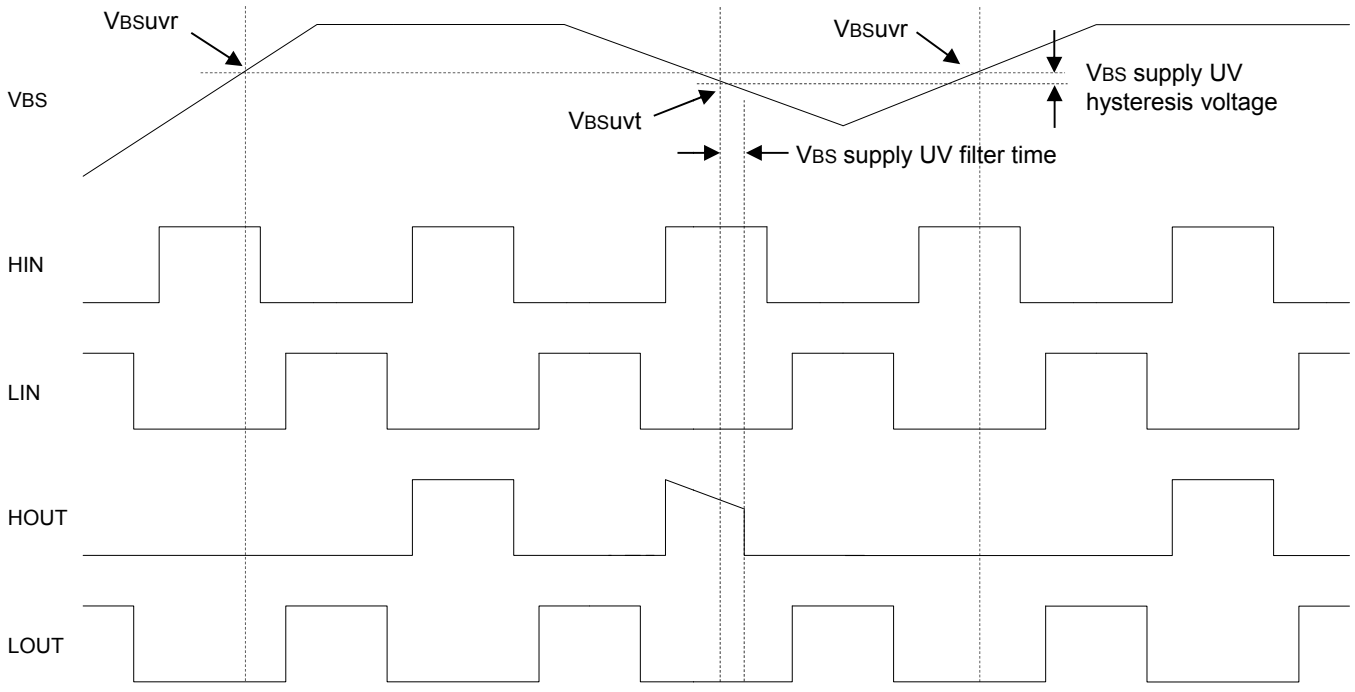
When the V_{CC} supply voltage is lower than power reset trip voltage, the power reset gets active and the outputs (LOUT) become "L". As soon as the V_{CC} supply voltage goes higher than the power reset trip voltage, the outputs will respond to the following active input signals.



Note1 :Delay times between input and output signals are not shown in the figure above.

5. HIGH SIDE V_{BS} SUPPLY UNDER VOLTAGE LOCKOUT SEQUENCE

When V_{BS} supply voltage drops below the V_{BS} supply UV trip voltage and the duration in this status exceeds the V_{BS} supply UV filter time, the output of the high side is locked. As soon as the V_{BS} supply voltage rises above the V_{BS} supply UV reset voltage, the output will respond to the following active HIN signal.

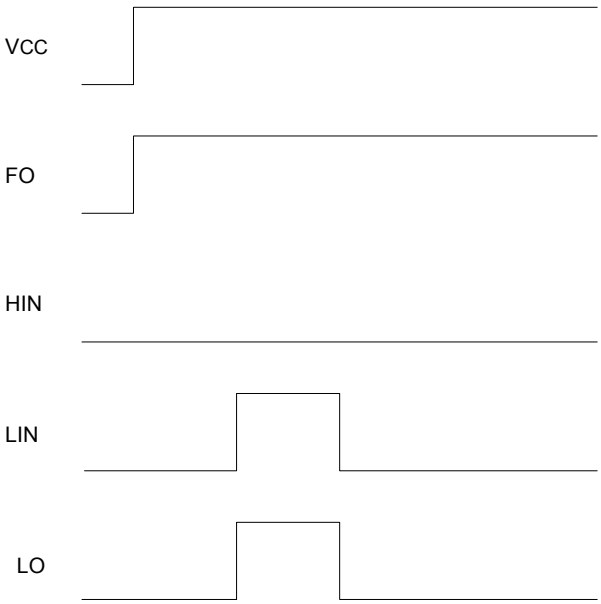


Note1 :Delay times between input and output signals are not shown in the figure above.

6. POWER START-UP SEQUENCE

At power supply start-up the following sequence is recommended when bootstrap supply topology is used.

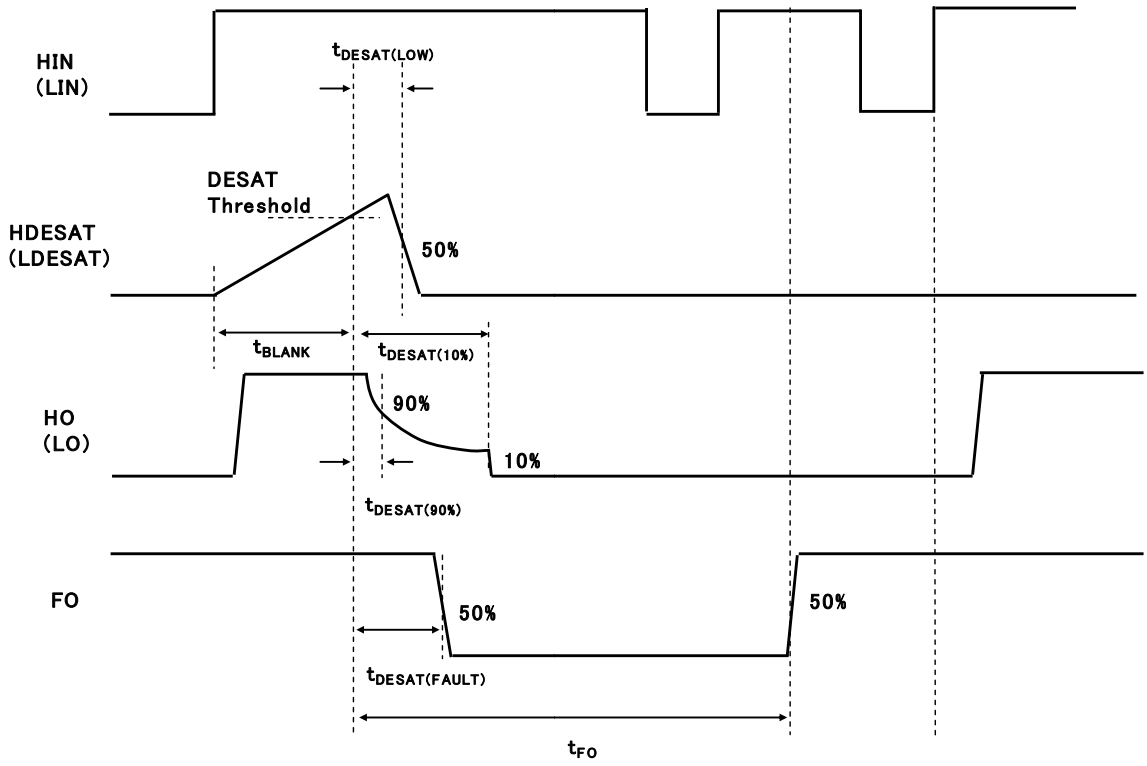
(1). Apply V_{CC}.
(2). Make sure that FO is at high level.
(3). Set LIN to high level and HIN to low level so that bootstrap capacitor could be charged.
(4). Set LIN to low level.



Note : If two power supply are used for supplying V_{CC} and V_{BS} individually, it is recommended to set V_{CC} first and then set V_{BS}.

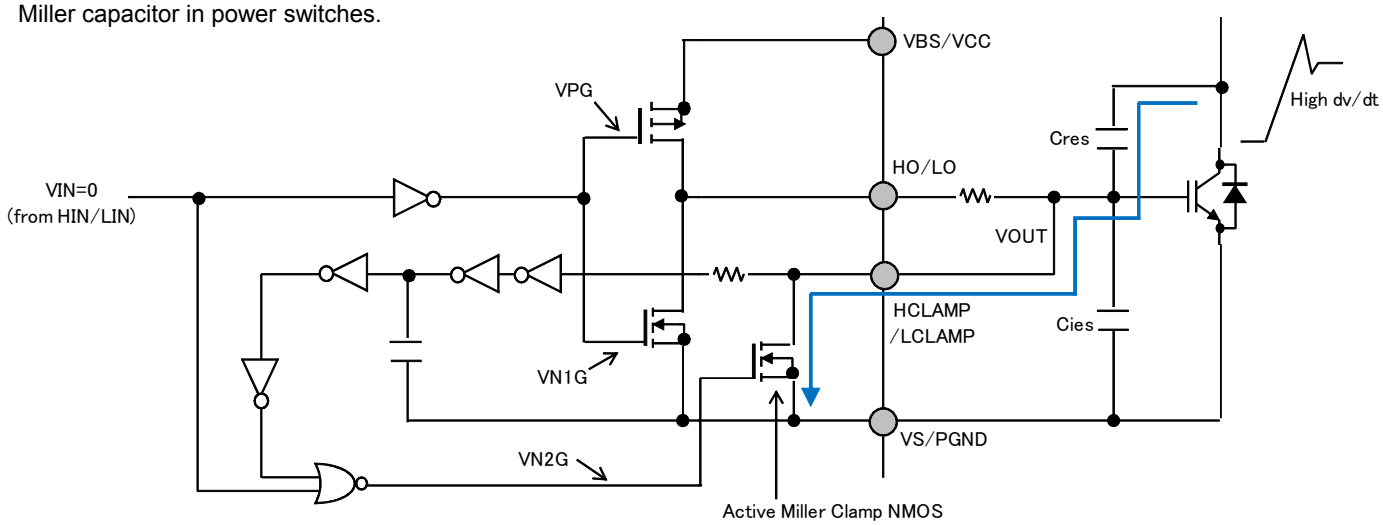
7. DESATURATION DETECTION AND HIGH CURRENT PROTECTION

HDESAT(LDESAT) detects the IGBT Vce voltage. When the IGBT is ON and the DESAT voltage exceeds DESAT threshold voltage, HO(LO) output slowly falls to a low level to softly turn-off the IGBT and prevent high di/dt noises. And FO output falls to a low level to transmit the fault signal to the micro controller. Once the fault condition is detected, all input signals are ignored during the t_{FO} period to complete the soft shutdown.

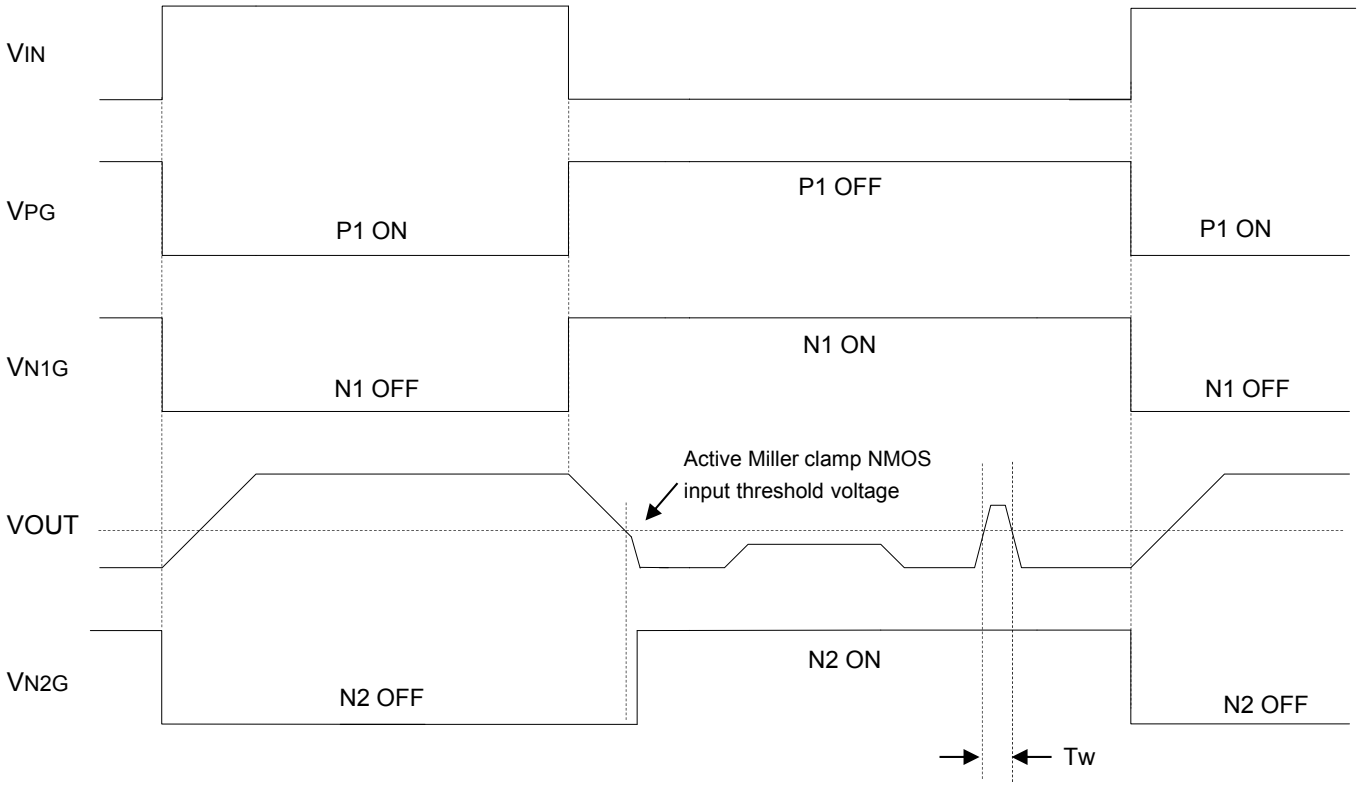


8. ACTIVE MILLER EFFECT CLAMP NMOS OUTPUT TIMING DIAGRAM

The structure of the output driver stage is shown in following figure. This circuit structure employs a solution for the problem of the Miller current through Cres in IGBT switching applications. Instead of driving the IGBT gate to a negative voltage to increase the safety margin, this circuit structure uses a NMOS to establish a low impedance path to prevent the self-turn-on due to the parasitic Miller capacitor in power switches.

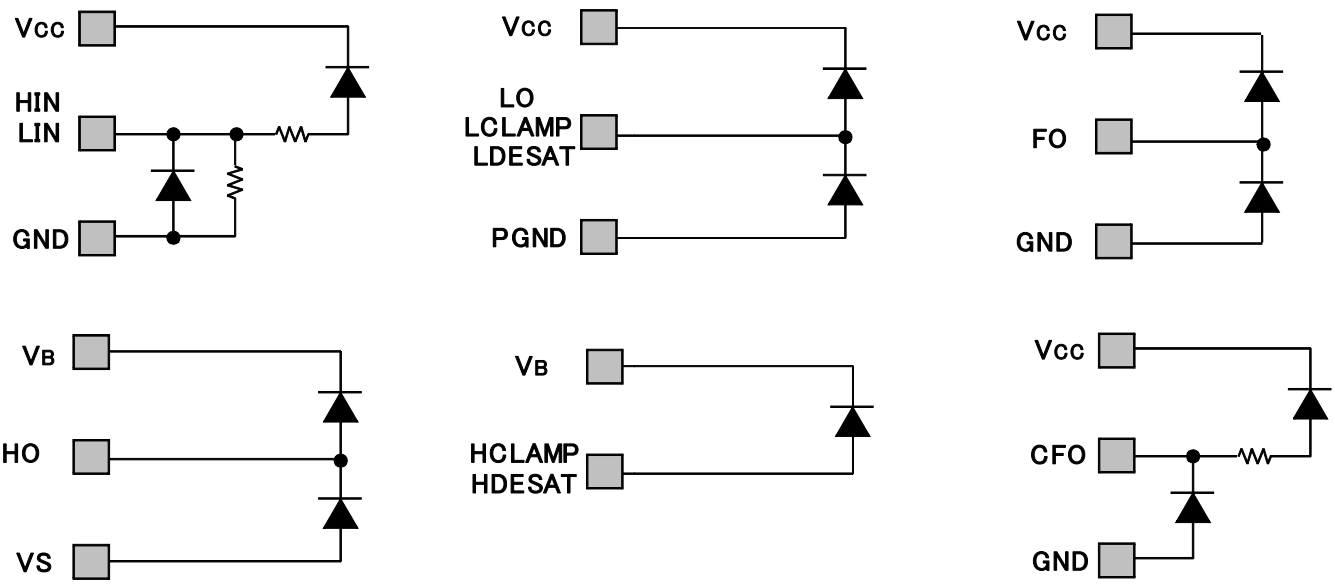


When HIN/LIN is at low level and the voltage of the VOUT (IGBT gate voltage) is below active Miller effect clamp NMOS input threshold voltage, the active Miller effect clamp NMOS is being turned on and opens a low resistive path for the Miller current through Cres.



Active Miller effect clamp NMOS keeps turn-on if T_W does not exceed active Miller clamp NMOS filter time

INTERNAL DIODE CLAMP CIRCUITS FOR INPUT AND OUTPUT PINS

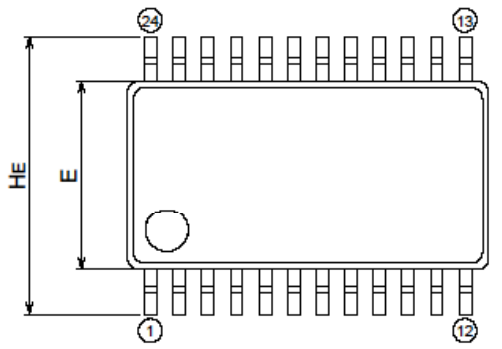


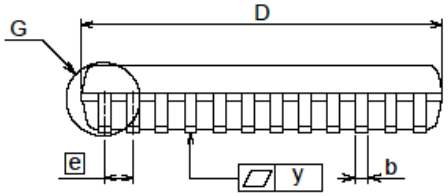
ENVIRONMENTAL CONSCIOUSNESS

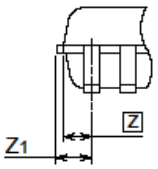
M81748FP is compliant with the Restriction of the Use of Certain Hazardous Substances in Electrical and Electronic Equipment (RoHS) directive 2011/65/EU.

PACKAGE OUTLINE

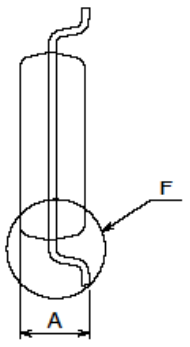
EIAJ Package Code	JEDEC Code	Weight(g)	Lead Material
SSOP24-P-300-0.80	–	0.2	Cu Alloy

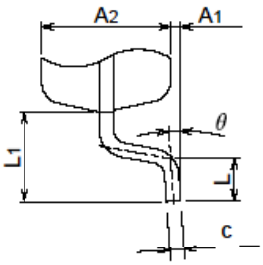




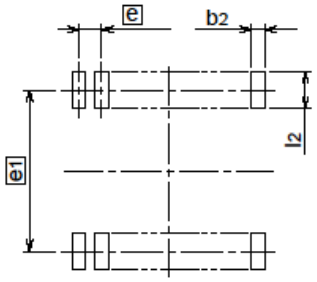


Detail G





Detail F



Recommended Mount Pad

Symbol	Dimension in Millimeters		
	Min	Nom	Max
A	–	–	2.1
A1	0	0.1	0.2
A2	–	1.8	–
b	0.3	0.35	0.45
c	0.18	0.2	0.25
D	10.0	10.1	10.2
E	5.2	5.3	5.4
e	–	0.8	–
HE	7.5	7.8	8.1
L	0.4	0.6	0.8
L1	–	1.25	–
Z	–	0.65	–
Z1	–	–	0.8
y	–	–	0.1
θ	0°	–	8°
b2	–	0.5	–
e1	–	7.62	–
l2	1.27	–	–

Main Revision for this Edition

No.	Date	Revision	
		Pages	Points
A	3, Feb. 2015	-	New making

Keep safety first in your circuit designs!

Mitsubishi Electric Corporation puts the maximum effort into making semiconductor products better and more reliable, but there is always the possibility that trouble may occur with them. Trouble with semiconductors may lead to personal injury, fire or property damage. Remember to give due consideration to safety when making your circuit designs, with appropriate measures such as (i) placement of substitutive, auxiliary circuits, (ii) use of non-flammable material or (iii) prevention against any malfunction or mishap.

Notes regarding these materials

- These materials are intended as a reference to assist our customers in the selection of the Mitsubishi semiconductor product best suited to the customer's application; they do not convey any license under any intellectual property rights, or any other rights, belonging to Mitsubishi Electric Corporation or a third party.
- Mitsubishi Electric Corporation assumes no responsibility for any damage, or infringement of any third-party's rights, originating in the use of any product data, diagrams, charts, programs, algorithms, or circuit application examples contained in these materials.
- All information contained in these materials, including product data, diagrams, charts, programs and algorithms represents information on products at the time of publication of these materials, and are subject to change by Mitsubishi Electric Corporation without notice due to product improvements or other reasons. It is therefore recommended that customers contact Mitsubishi Electric Corporation or an authorized Mitsubishi Semiconductor product distributor for the latest product information before purchasing a product listed herein.
  The information described here may contain technical inaccuracies or typographical errors. Mitsubishi Electric Corporation assumes no responsibility for any damage, liability, or other loss rising from these inaccuracies or errors.
  Please also pay attention to information published by Mitsubishi Electric Corporation by various means, including the Mitsubishi Semiconductor home page (http://www.MitsubishiElectric.com/).
- When using any or all of the information contained in these materials, including product data, diagrams, charts, programs, and algorithms, please be sure to evaluate all information as a total system before making a final decision on the applicability of the information and products. Mitsubishi Electric Corporation assumes no responsibility for any damage, liability or other loss resulting from the information contained herein.
- Mitsubishi Electric Corporation semiconductors are not designed or manufactured for use in a device or system that is used under circumstances in which human life is potentially at stake. Please contact Mitsubishi Electric Corporation or an authorized Mitsubishi Semiconductor product distributor when considering the use of a product contained herein for any specific purposes, such as apparatus or systems for transportation, vehicular, medical, aerospace, nuclear, or undersea repeater use.
- The prior written approval of Mitsubishi Electric Corporation is necessary to reprint or reproduce in whole or in part these materials.
- If these products or technologies are subject to the Japanese export control restrictions, they must be exported under a license from the Japanese government and cannot be imported into a country other than the approved destination.
  Any diversion or re-export contrary to the export control laws and regulations of Japan and/or the country of destination is prohibited.
- Please contact Mitsubishi Electric Corporation or an authorized Mitsubishi Semiconductor product distributor for further details on these materials or the products contained therein.

© 2015 MITSUBISHI ELECTRIC CORPORATION. ALL RIGHTS RESERVED.